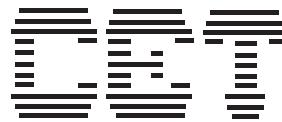


CEM9945



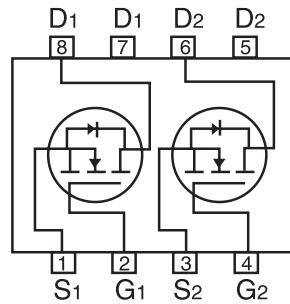
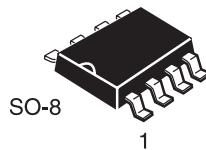
March 1998

Dual N-Channel Enhancement Mode Field Effect Transistor

5

FEATURES

- 60V , 3.3A , $R_{DS(ON)}=100m\Omega$ @ $V_{GS}=10V$.
 $R_{DS(ON)}=200m\Omega$ @ $V_{GS}=4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ^a @ $T_J=125^\circ C$ -Pulsed ^b	I_D	± 3.3	A
	I_{DM}	± 10	A
Drain-Source Diode Forward Current ^a	I_S	1.7	A
Maximum Power Dissipation ^a	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	$^\circ C/W$
--	-----------------	------	--------------

CEM9945

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$ unless otherwise noted)

5

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V_{BDSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DS(0)}$	$V_{DS}=48V, V_{GS}=0V$		1		μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D = 250\mu A$	1	1.4	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D = 3.3A$		0.06	0.1	Ω
		$V_{GS}=4.5V, I_D = 2.5A$		0.08	0.2	Ω
On-State Drain Current	$I_{D(ON)}$	$V_{GS} = 10V, V_{DS} = 5V$	10			A
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 3.3A$		7		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS} = 0V$ $f = 1.0MHz$		428	560	pF
Output Capacitance	C_{oss}			128	170	pF
Reverse Transfer Capacitance	C_{rss}			28	40	pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V,$ $I_D = 1A,$ $R_L = 30\Omega$ $V_{GEN} = 10V,$ $R_{GEN} = 6\Omega$		7	25	ns
Rise Time	t_r			3	30	ns
Turn-Off Delay Time	$t_{D(OFF)}$			22	50	ns
Fall Time	t_f			6	40	ns
Total Gate Charge	Q_g	$V_{DS} = 30V, I_D = 3.3A,$ $V_{GS} = 10V$		9	30	nC
Gate-Source Charge	Q_{gs}			2		nC
Gate-Drain Charge	Q_{gd}			4		nC

CEM9945

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

5

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 1.7A		0.8	1.2	V

Notes

- a. Surface Mounted on FR4 Board, t ≤ 10sec.
- b. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- c. Guaranteed by design, not subject to production testing.

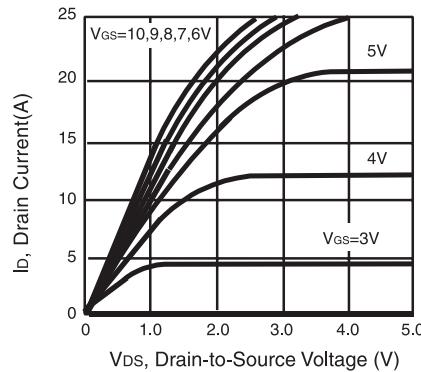


Figure 1. Output Characteristics

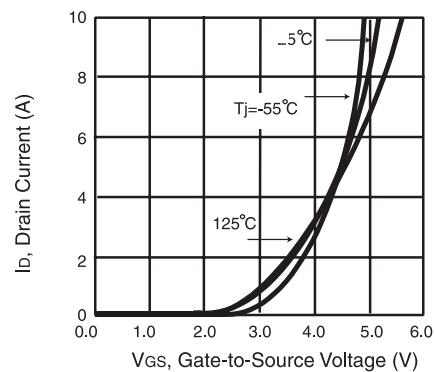


Figure 2. Transfer Characteristics

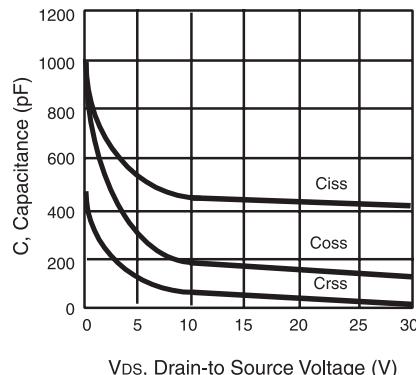


Figure 3. Capacitance

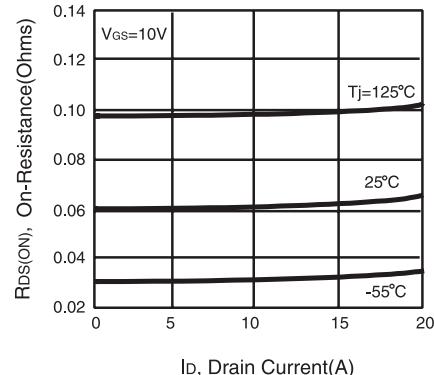


Figure 4. On-Resistance Variation with Drain Current and Temperature

CEM9945

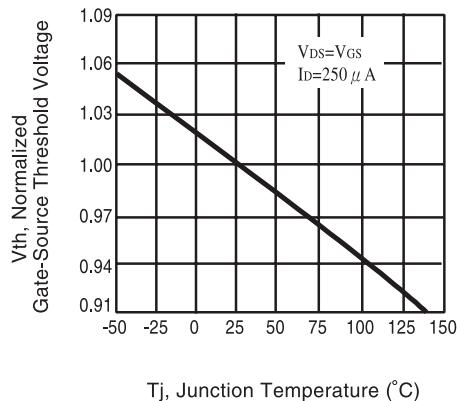
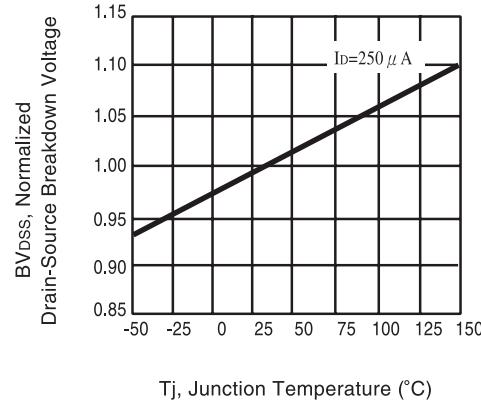
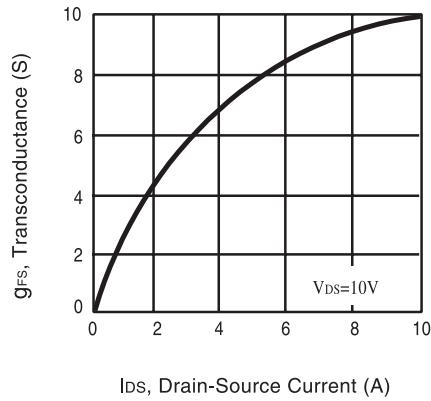


Figure 5. Gate Threshold Variation with Temperature



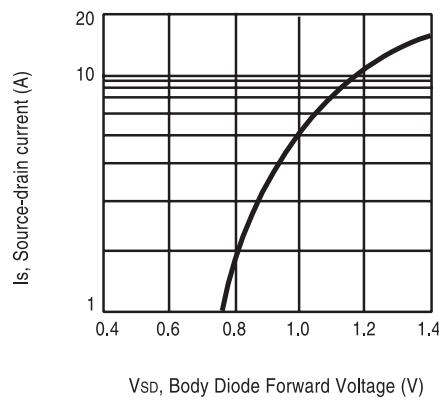
5

Figure 6. Breakdown Voltage Variation with Temperature



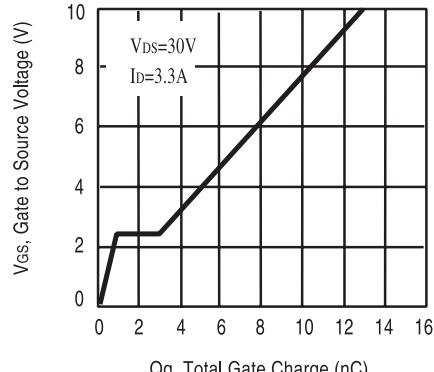
I_d, Drain-Source Current (A)

Figure 7. Transconductance Variation with Drain Current



I_s, Source-drain current (A)

Figure 8. Body Diode Forward Voltage Variation with Source Current



V_{gs}, Gate to Source Voltage (V)

Figure 9. Gate Charge

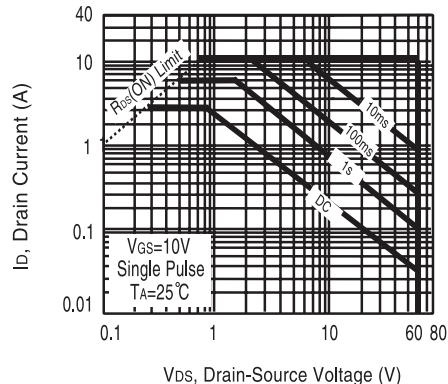


Figure 10. Maximum Safe Operating Area

CEM9945

5

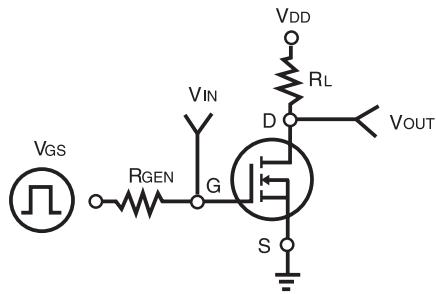


Figure 11. Switching Test Circuit

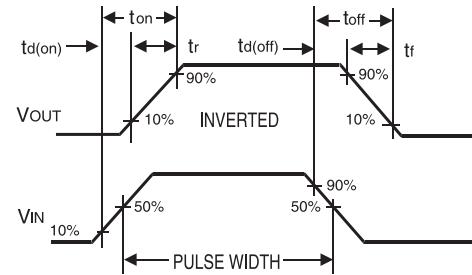


Figure 12. Switching Waveforms

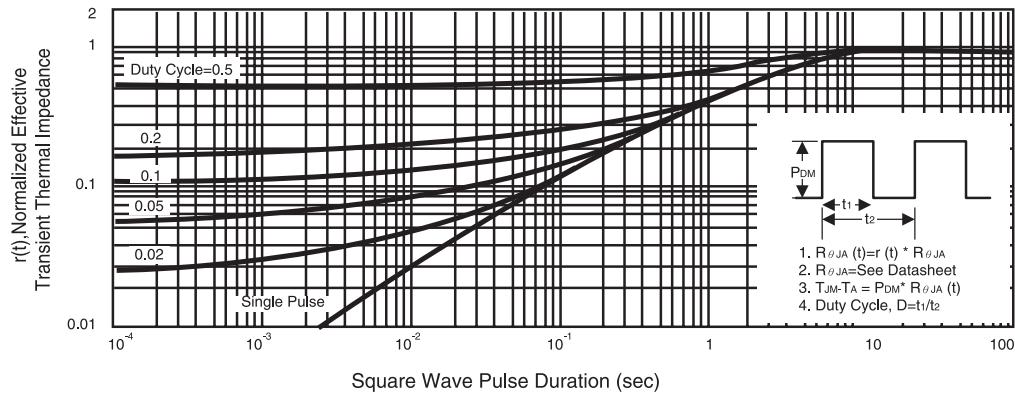


Figure 13. Normalized Thermal Transient Impedance Curve